

Attorney's Docket No.: 07977/204002/US3480D1

E1 could
a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film; and a second insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer.

E2
22. (Amended) A semiconductor device according to claim 21, wherein said first insulating film is a gate insulating film comprising silicon oxide.

E3 could
25. (Amended) A semiconductor device comprising:
a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;
a first insulating film formed on said gate electrode;
a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film, and

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a second insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

26. (Amended) A semiconductor device according to claim 25, wherein said insulating film is a gate insulating film comprising silicon oxide.